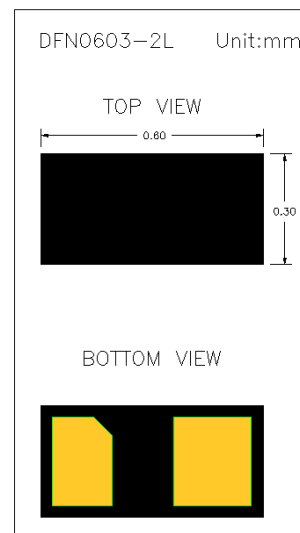
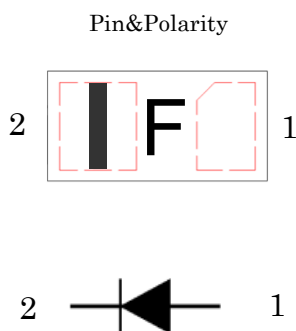


Schottky Diode

- ◇ Low current rectification
- ◇ Low forward voltage
- ◇ ROHS Compliant
- ◇ UL-94 V-0 / Green EMC
- ◇ AEC-Q101 qualified

Device Marking Code	
RB521D3-30	F



Maximum Ratings (Ta = 25 °C)

Symbol	Parameter	Value	Units
P_D	Power Dissipation	100	mW
V_R	Reverse Voltage	30	V
$I_{F(AV)}$	Average Forward Current	100	mA
I_{FSM}	Non-Repetitive Peak Forward Current *1	500	mA
T_J	Junction Temperature	125	°C
T_{STG}	Storage Temperature	-55 to +125	°C

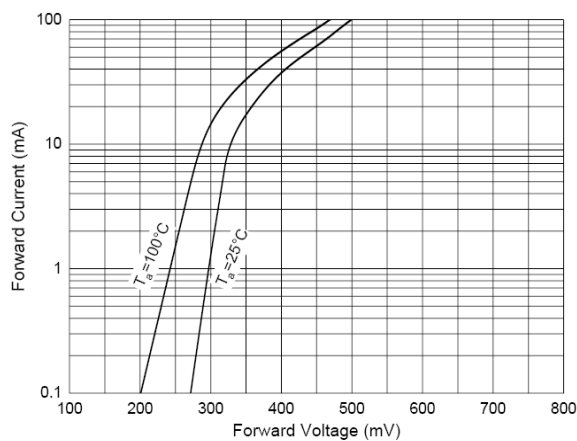
*1: 8.3ms Single Half Sine-Wave

Electrical Characteristics (Ta = 25 °C unless otherwise noted)

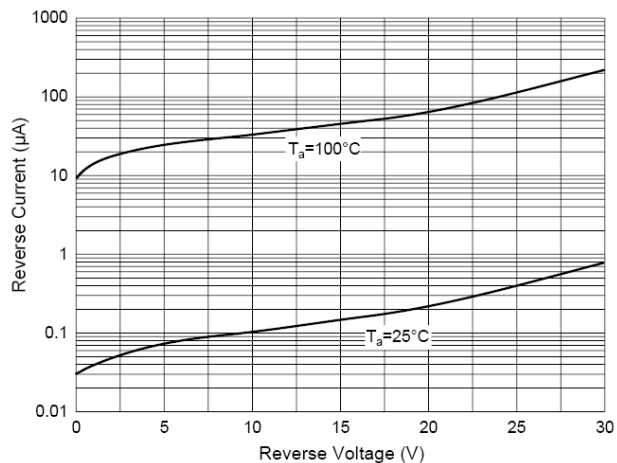
Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_R	Reverse Leakage Current	$V_R=10V$	—	—	10	uA
		$V_R=30V$	—	—	50	
V_F	Forward Voltage	$I_F=10mA$	—	—	0.38	V
		$I_F=100mA$	—	0.46	0.53	
V_R	Reverse Voltage	$I_R=50uA$	30	—	—	V

Schottky Diode

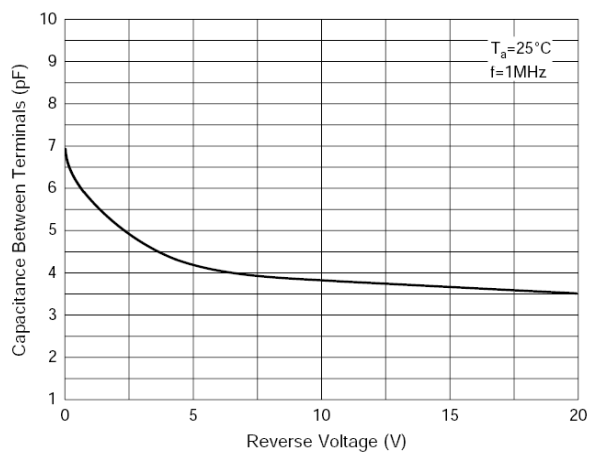
Typical Characteristics



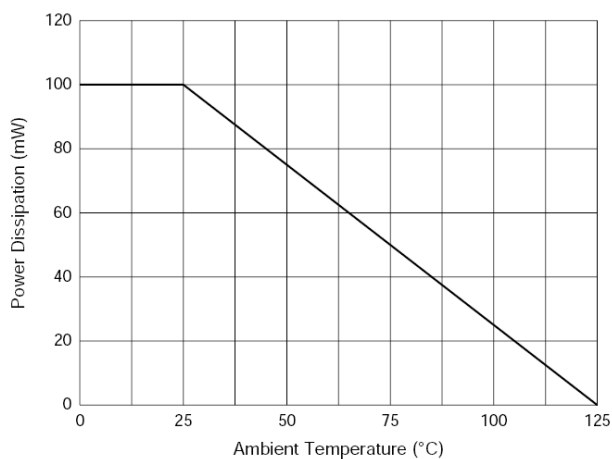
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

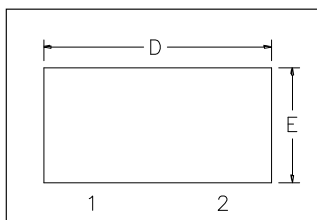
Schottky Diode

Ordering Information

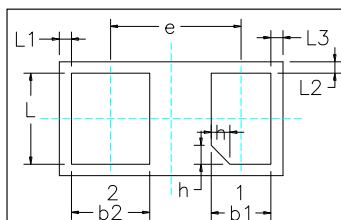
Device	Package	Shipping	Tape wide	Emboss pitch	Tape specification	Notes
RB521D3-30	DFN0603-2L	Tape & Reel 15000pcs /7" Reel	8mm	4mm	Conductive	

Package outline : DFN0603-2L

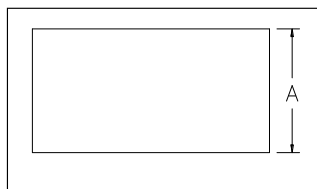
Top view



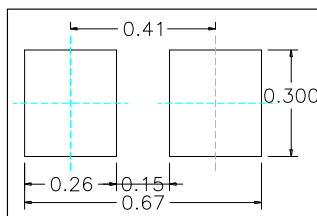
Bottom view



Side view



Soldering Pattern



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.28	0.30	0.32
b1	0.13	0.18	0.23
b2	0.14	0.19	0.24
D	0.55	0.60	0.65
e	0.350BSC		
L1	0.030BSC		
L2	0.025BSC		
L3	0.035BSC		
E	0.25	0.30	0.35
L	0.20	0.25	0.30
h	0.00	0.05	0.10

Notice:

1. Lead no need to do plating
2. Other Tolerance: ± 0.05
3. Dimensions are exclusive of Burrs, Mold Flash and Tie Bar extrusions
4. Unit: mm